

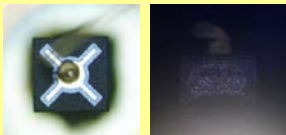
LED chip type

Notes ; These photos are CCD images of 850nm infrared LED. These colors are not true for the human eye.


Chip type A

- Conventional LED
- Liquid Phase Epitaxy
- Variety of material and wavelength

Off




On



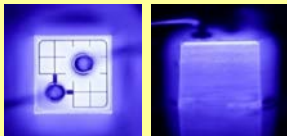
Chip type B

- Transparent type LED
- Vapor Phase Epitaxy
- High light output power
- Two bonding pads on top side

Off



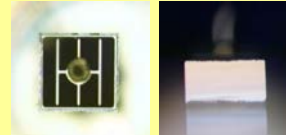
On



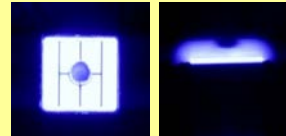
Chip type C

- Reflection type LED
- Vapor Phase Epitaxy
- High light output power
- Strong vertical light

Off



On



Visible LED chip list (565-700nm)

Chip type	Structure (Epi/Sub)	Product	Polarity	Wavelength		Chip size		Characteristics				Plant ※
				(nm)	Symbol	X & Y (μm)	Z (μm)	IF (mA)	IV (mcd)	Power (mW)	VF (V)	
A	GaP/GaP	L-34P-V(HCL)	P-up	565	Hue	260	270	20	10.0	-	2.20	ROK
		L-34PY-W(HCL)	P-up	567	Hue	230	270	20	10.0	-	2.20	ROK
		L-35PH-V(HCL)	P-up	570	Hue	260	270	20	14.0	-	2.20	ROK
		L-22P-W(HCL)	P-up	700	Hue	230	270	20	0.7	-	2.25	ROK
	GaAsP/GaP	SLYAH-W	P-up	588	Hue	240	270	20	8.0	-	2.10	ROK
		SLSS-W	P-up	615	Hue	240	270	20	5.0	-	2.10	ROK
		SLOSH-X	P-up	630	Hue	230	220	20	6.3	-	2.10	ROK
		SLRSH-W	P-up	645	Hue	240	270	20	4.0	-	2.00	ROK
	AlGaAs/GaAs	AR-26	N-up	660	Hue	230	270	20	7.0	-	1.80	ROK
		ARH-260	N-up	660	λp	235	240	20	13.0	-	1.80	RPC
		ARH-300B	N-up	660	λp	275	280	20	15.5	-	1.80	RPC
	AlGaAs/AlGaAs	ARS-30	N-up	660	Hue	330	120	20	18.0	-	1.80	ROK
ARU-35		P-up	660	λp	325	180	20	33.0	-	1.80	RPC	
ABU-35		P-up	670	λp	325	180	20	-	2.4	1.80	RPC	
B	AlGaInP/GaP	GYA-280H	P, N up	590	λd	270	270	20	500	-	2.20	ROK
		GYA-340BH	P, N up	590	λd	330	270	20	430	-	2.20	ROK
		GOC-280	P, N up	605	λd	280	270	20	500	-	2.20	ROK
		HOB-350F	P, N up	620	λd	325	270	20	800	-	2.10	ROK
		GOA-340B	P, N up	620	λd	330	270	20	400	-	2.20	ROK
		GOA-350	P, N up	620	λd	325	270	20	450	-	2.10	ROK
		GOD-230T	P, N up	625	λd	220	200	20	450	-	2.20	ROK
		GOD-280	P, N up	625	λd	280	270	20	300	-	2.20	ROK
		GRA-315H	P, N up	630	λd	295	270	20	400	-	2.10	ROK
		HRP-350F	P, N up	660	λp	325	270	20	-	11.0	2.10	ROK
C	AlGaInP/Si	R6D-52SSC	N-up	615	λd	500	190	150	6,000	-	2.20	RPC
	AlGaInP/Ge	R66-26GSA	N-up	660	λp	240	190	20	-	11.5	2.00	RPC
		R66-35GSA	N-up	660	λp	330	190	20	-	13.0	1.90	RPC
		R69-52GSA	N-up	685	λp	500	190	140	-	100	2.10	RPC

※ RPC : Resonac Photonics Corporation (Location/Saitama-Pref.) ROK : Resonac Optoelectronics Kagoshima Corporation(Location/Kagoshima-Pref.)

The data on this page are examples measured at RESONAC PHOTONICS and RESONAC OPTOELECTRONICS KAGOSHIMA, and they are not guaranteed. RESONAC PHOTONICS reserves the right to introduce changes without notice.

Infrared LED chip list (700-970nm)

Chip type	Structure (Epi/Sub)	Product	Polarity	Peak wavelength (nm)	Chip size		Characteristics			Plant ※
					X & Y (μm)	Z (μm)	IF (mA)	Power (mW)	VF (V)	
A	AlGaAs/GaAs	BRH-35	N-up	700	325	280	20	1.10	1.75	RPC
		BCH-260	N-up	730	235	240	20	1.30	1.70	RPC
		CBH-260	N-up	770	235	250	20	1.25	1.64	RPC
		CBH-35	N-up	770	325	280	20	1.10	1.70	RPC
		CR-35	N-up	830	325	280	20	0.80	1.70	RPC
		CRH-35	N-up	830	325	280	20	1.00	1.50	RPC
		DCK-260B	P-up	850	240	230	10	0.96	1.45	RPC
		DCK-300B	P-up	850	280	230	10	0.97	1.45	RPC
		IR-260C	P-up	940	235	240	20	1.70	1.28	RPC
		IR-44	P-up	940	185	180	20	0.75	1.30	ROK
		IR-46	P-up	945	205	180	20	1.20	1.25	ROK
		IRH-280SB	P-up	940	260	240	20	2.00	1.25	RPC
		IRH-35M	P-up	940	325	280	20	2.20	1.20	RPC
		IRH-46	P-up	940	205	180	20	1.80	1.25	ROK
	IRN-260C	N-up	950	240	230	20	1.30	1.30	RPC	
	AlGaAs/AlGaAs	DCP-260D	P-up	850	240	190	10	1.40	1.45	ROK
		DCP-260SB	P-up	850	240	200	10	1.60	1.45	RPC
		DCP-35J	P-up	850	325	190	20	5.30	1.43	RPC
		DPA-350MJ	P-up	865	325	190	20	5.00	1.38	RPC
		DXA-300J	N-up	870	275	190	20	5.00	1.55	RPC
		DSX-350J	N-up	870	325	190	20	3.80	1.40	RPC
		DR-300UC	N-up	880	280	200	10	0.90	1.27	RPC
		DR-40	N-up	880	375	260	20	1.60	1.30	RPC
		DRH-35	N-up	880	325	210	20	2.00	1.35	RPC
KM89528NF		N-up	895	265	210	20	3.60	1.33	ROK	
KM89528NFMA-A	N-up	895	265	210	20	4.20	1.33	ROK		
FR-35	N-up	910	325	260	20	1.50	1.28	RPC		
KM91028NF	N-up	910	265	175	20	3.80	1.37	ROK		
KM91028NFMA-A	N-up	910	265	175	20	4.30	1.37	ROK		
C	AlGaAs/Ge	R78-35GSE	N-up	780	330	190	20	8.00	1.60	RPC
		R81-35GSE	N-up	810	330	190	20	8.00	1.55	RPC
		R85-26GSE	N-up	850	240	190	20	7.50	1.60	RPC
		R85-35GSE	N-up	850	330	190	20	8.50	1.50	RPC
		R85-52GSE	N-up	850	500	190	20	7.50	1.40	RPC
		R87-35GSE	N-up	870	330	190	20	8.00	1.45	RPC
		R94-35GSE	N-up	940	330	190	20	7.00	1.40	RPC
		R97-35GSE	N-up	970	330	190	20	7.00	1.40	RPC
	AlGaAs/Ge	P85-26ATA	P-up	850	240	265	20	8.00	1.55	RPC
		P85-26GTA	P-up	850	240	190	20	8.00	1.55	RPC
	AlGaAs/Ge (Double Junction)	R81-110GWS	N-up	810	1,080	190	1,000	700	3.40	RPC
		R85-110GWS	N-up	850	1,080	190	1,000	750	3.20	RPC
		R94-110GWS	N-up	940	1,080	190	1,000	680	3.00	RPC

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